

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	126	(fusi (full\$3 near2 silicid\$8)) and (gate electrode control) and ((work adj function) cmos complementary pmos nmos channel)	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/20 13:21
L3	143	(fusi (full\$3 near2 silicid\$8)) same (gate electrode control) same (work adj function) same (cmos complementary pmos nmos channel)	US-PGPUB; USPAT	OR	ON	2009/05/20 14:30
L4	10812	257/369.ccls. 257/388.ccls. 257/407.ccls. 257/410.ccls. 257/411.ccls. 257/412.ccls. 257/ e21.199.ccls. 257/ e29.161.ccls. 438/216. ccls. 438/287.ccls. 438/591.ccls. 438/592.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/05/20 14:38
L5	21	L4 and ((ptsi cosi zrsi tasi tisi vsi hfsl ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid \$8 disilicide))) same ((gate electrode control) with (insulat \$6 dielectric oxide dioxide) with (high near2 (k permittivity (dielectric adj constant)))) same (cmos complementary pmos nmos channel))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/05/20 14:38

L6	59	L4 and (((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid \$8 disilicide))) with (full\$3 entir\$6 completely anneal\$6 heat\$6 treat\$6 rta rtp thermal\$6)) same (gate electrode control) same (insulat \$6 dielectric oxide dioxide) same (cmos complementary pmos nmos channel))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/05/20 14:42
L7	55	((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid\$8 disilicide))) with (gate electrode control)) same ((insulat\$6 dielectric oxide dioxide) with (high near2 (k permittivity (dielectric adj constant)))) same (cmos complementary pmos nmos channel))	US-PGPUB; USPAT	OR	ON	2009/05/20 14:43
L8	17	((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid\$8 disilicide))) with (full \$3 entir\$6 completely (direct\$6 near2 contact\$6)) with (anneal\$6 heat\$6 treat\$6 rta rtp thermal \$6)) same (gate electrode control) same (insulat\$6 dielectric oxide dioxide) same (cmos complementary pmos nmos channel))	US-PGPUB; USPAT	OR	ON	2009/05/20 14:45

L9	15	((ptsi cosi zrsl tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid\$8 disilicide))) with (gate electrode control)) and ((insulat\$6 dielectric oxide dioxide) with (high near2 (k permittivity (dielectric adj constant)))) and (cmos complementary pmos nmos channel))	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/20 14:46
L10	39	(ptsi cosi zrsl tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid\$8 disilicide))) and (full \$3 entir\$6 completely (direct\$6 near2 contact\$6)) and (anneal\$6 heat\$6 treat\$6 rta rtp thermal \$6) and (gate electrode control) and (insulat\$6 dielectric oxide dioxide) and (cmos complementary pmos nmos channel))	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/20 14:50
L11	44	((((ptsi cosi zrsl tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium metal) near2 (silicid \$8 disilicide))) near4 (gate electrode control)) and ((insulat \$6 dielectric oxide dioxide) with (high near2 (k permittivity (dielectric adj constant)))) and (cmos complementary pmos nmos channel)).clm.	US-PGPUB	OR	ON	2009/05/20 15:00

L12	506	((((ptsi cosi zrasi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium metal) near2 (silicid \$8 disilicide))) near4 (gate electrode control)) and (insulat \$6 dielectric oxide dioxide) and (fusi (full \$3 near2 silicid\$8) direct\$6 contact\$6 physical\$6)).clm.	US-PGPUB	OR	ON	2009/05/20 15:03
L13	369	((((ptsi cosi zrasi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium metal) near2 (silicid \$8 disilicide))) near4 (gate electrode control)) and ((insulat \$6 dielectric oxide dioxide) near2 gate) and (fusi (full\$3 near2 silicid\$8) direct \$6 contact\$6 physical \$6) and (substrate silicon semiconductor wafer)).clm.	US-PGPUB	OR	ON	2009/05/20 15:06
L14	93	((((ptsi cosi zrasi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium metal) near2 (silicid \$8 disilicide))) near4 (gate electrode control)) and (((insulat\$6 dielectric oxide dioxide) near2 gate) near4 (fusi (full \$3 near2 silicid\$8) direct\$6 contact\$6 physical\$6)) and (substrate silicon semiconductor wafer)).clm.	US-PGPUB	OR	ON	2009/05/20 15:07

L15	93	(((nisi ni3si "ni. sub.3si" "ni.sub.3 si" nisi2 "nisi. sub.2" (nickel near2 silicid\$8)) near4 (gate electrode control)) and ((insulat\$6 dielectric oxide dioxide) near2 gate) and (substrate silicon semiconductor wafer)).clm.	US-PGPUB	OR	ON	2009/05/20 15:16
L16	59	(((nisi ni3si "ni. sub.3si" "ni.sub.3 si" nisi2 "nisi. sub.2" (nickel near2 silicid\$8)) near4 (gate electrode control)) and ((insulat\$6 dielectric oxide dioxide) near2 gate) and (fusi (full\$3 near2 silicid\$8) direct \$6 contact\$6 physical \$6) and (substrate silicon semiconductor wafer)).clm.	US-PGPUB	OR	ON	2009/05/20 15:17
S35	359	257/407.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/05/20 11:40
S36	10812	257/369.ccls. 257/388.ccls. 257/407.ccls. 257/410.ccls. 257/411.ccls. 257/412.ccls. 257/ e21.199.ccls. 257/ e29.161.ccls. 438/216. ccls. 438/287.ccls. 438/591.ccls. 438/592.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/05/20 11:47
S37	357	S36 and (fusi (full\$3 near2 silicid\$8))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/05/20 11:47

S38	285	S36 and ((nisi ni3si "ni.sub.3si" "ni.sub.3si" nisi2 "nisi.sub.2" (nickel near2 silicid\$8)) same (gate electrode control) same (cmos complementary pmos nmos channel))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/05/20 12:03
S39	27	(ni3si "ni.sub.3si") and (gate electrode control cmos complementary pmos nmos channel)	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/20 12:11
S40	85	(ni3si "ni.sub.3si") same (gate electrode control cmos complementary pmos nmos channel)	US-PGPUB; USPAT	OR	ON	2009/05/20 12:12

5/20/09 3:22:44 PM

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